2SC2632

Silicon NPN epitaxial planar type

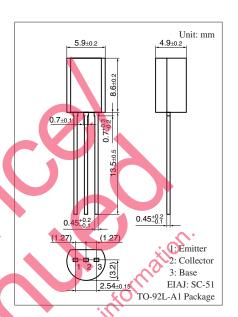
For low-frequency high breakdown voltage amplification Complementary to 2SA1124

■ Features

- Satisfactory linearity of forward current transfer ratio h_{FE}
- High collector-emitter voltage (Base open) V_{CEO}
- \bullet Small collector output capacitance (Common base, input open circuited) C_{ob}

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	150	V	
Collector-emitter voltage (Base open)	V _{CEO}	150	V	
Emitter-base voltage (Collector open)	V_{EBO}	5	V	
Collector current	I_C	50	mA	
Peak collector current	I _{CP}	100	mA	
Collector power dissipation	P _C	1	W	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

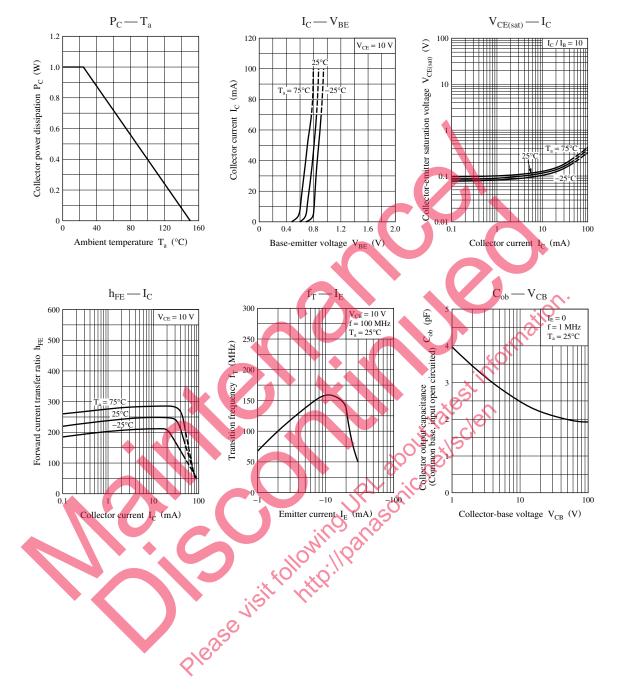
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 100 \mu A, I_{\rm B} = 0$	150			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\rm E} = 10 \mu \text{A} \cdot I_{\rm C} = 0$	5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 100 \text{ V}, I_{f_a} = 0$			1	μΑ
Forward current transfer ratio *	h_{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	130		330	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 30 \text{ mA}, I_B = 3 \text{ mA}$			1	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -10 \text{ mA}, f = 200 \text{ MHz}$		160		MHz
Collector output capacitance	ob	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$			3	pF
(Common base, input open circuited)	9					
Noise voltage	NV	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}, G_{V} = 80 \text{ dB}$		150	300	mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S
h_{FE}	130 to 220	185 to 330

Collector-base voltage V_{CB} (V)



2 SJC00118BED

Collector current I_C (mA)

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